

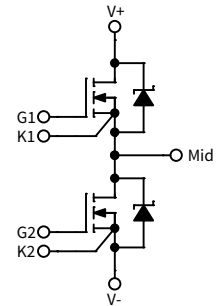
WAS350M12BM3, WAS350M12BM3T

1200 V, 350 A, Silicon Carbide, Half-Bridge Module

| | |
|----------|--------|
| V_{DS} | 1200 V |
| I_{DS} | 350 A |

Technical Features

- Industry Standard 62 mm Footprint
- High Humidity Operation THB-80 (HV-H3TRB)
- Ultra Low Loss, High-Frequency Operation
- Zero Reverse Recovery from Diodes
- Zero Turn-off Tail Current from MOSFET
- Normally-off, Fail-safe Device Operation
- Copper Baseplate and Aluminum Nitride Insulator



Typical Applications

- Induction Heating
- Motor Drives
- Renewables
- Railway Auxiliary & Traction
- EV Fast Charging
- UPS and SMPS

System Benefits

- 62 mm Form Factor Enables System Retrofit
- Increased System Efficiency, due to Low Switching & Conduction Losses of SiC

Key Parameters

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions | Note |
|--|---------------|------|--------|------|------------------|--|--------------------------|
| Drain-Source Voltage | V_{DS} | | | 1200 | V | | |
| Gate-Source Voltage, Maximum Value | $V_{GS(max)}$ | -10 | | +23 | | Transient | Note 1 Fig. 33 |
| Gate-Source Voltage, Recommended | $V_{GS(op)}$ | | -4/+15 | | | Static | |
| DC Continuous Drain Current | I_D | | 424 | | A | $V_{GS} = 15 \text{ V}, T_c = 25^\circ\text{C}, T_{vj} \leq 175^\circ\text{C}$ | Notes 2, 3 Fig. 21 |
| | | | 319 | | | $V_{GS} = 15 \text{ V}, T_c = 90^\circ\text{C}, T_{vj} \leq 175^\circ\text{C}$ | |
| DC Source-Drain Current (Schottky Diode) | $I_{SD(SD)}$ | | 440 | | | $V_{GS} = -4 \text{ V}, T_c = 25^\circ\text{C}, T_{vj} \leq 175^\circ\text{C}$ | |
| Pulsed Drain-Source Current | I_{DM} | | 700 | | | t_{pmax} limited by T_{vjmax} $V_{GS} = 15 \text{ V}, T_c = 25^\circ\text{C}$ | |
| Power Dissipation | P_D | | 1293 | | W | $T_c = 25^\circ\text{C}, T_{vj} \leq 175^\circ\text{C}$ | Note 4 Fig. 21 |
| Virtual Junction Temperature | $T_{vj(op)}$ | -40 | | 150 | $^\circ\text{C}$ | Operation | |
| | | | | 175 | | Intermittent with Reduced Life | |

Note (1): Recommended turn-on gate voltage is 15 V with $\pm 5\%$ regulation tolerance. Not for use in linear region.

Note (2): Current limit calculated by $I_{D(max)} = \sqrt{(P_D/R_{DS(typ)})(T_{vj(max)}/I_{D(max)})}$

Note (3): Verified by design

Note (4): $P_D = (T_{vj} - T_c)/R_{TH(jc,typ)}$

MOSFET Characteristics (Per Position) ($T_{VJ} = 25^\circ\text{C}$ Unless Otherwise Specified)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions | Note |
|--|---------------|------|-------------------|------|---------------------------|---|--------------------|
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | 1200 | | | | $V_{GS} = 0\text{ V}, T_{VJ} = -40^\circ\text{C}$ | |
| Gate Threshold Voltage | $V_{GS(th)}$ | 1.8 | 2.5 | 3.6 | V | $V_{DS} = V_{GS}, I_D = 85\text{ mA}$ | |
| | | | 2.0 | | | $V_{DS} = V_{GS}, I_D = 85\text{ mA}, T_{VJ} = 175^\circ\text{C}$ | |
| Zero Gate Voltage Drain Current | I_{DSS} | | 8.2 | 1128 | μA | $V_{GS} = 0\text{ V}, V_{DS} = 1200\text{ V}$ | |
| Gate-Source Leakage Current | I_{GSS} | | 40 | 400 | nA | $V_{GS} = 15\text{ V}, V_{DS} = 0\text{ V}$ | |
| Drain-Source On-State Resistance (Devices Only) | $R_{DS(on)}$ | | 4.0 | 5.2 | m Ω | $V_{GS} = 15\text{ V}, I_D = 350\text{ A}$ | Fig. 2 Fig. 3 |
| | | | 6.5 | | | $V_{GS} = 15\text{ V}, I_D = 350\text{ A}, T_{VJ} = 150^\circ\text{C}$ | |
| | | | 7.2 | | | $V_{GS} = 15\text{ V}, I_D = 350\text{ A}, T_{VJ} = 175^\circ\text{C}$ | |
| Transconductance | g_{fs} | | 306 | | S | $V_{DS} = 20\text{ V}, I_D = 350\text{ A}$ | Fig. 4 |
| | | | 292 | | | $V_{DS} = 20\text{ V}, I_D = 350\text{ A}, T_{VJ} = 150^\circ\text{C}$ | |
| Turn-On Switching Energy, $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$ $T_{VJ} = 150^\circ\text{C}$ | E_{ON} | | 5.0 4.5 4.4 | | mJ | $V_{DD} = 600\text{ V},$ $I_D = 350\text{ A},$ $V_{GS} = -4\text{ V}/15\text{ V},$ $R_{G(OFF)} = 0.5\ \Omega, R_{G(ON)} = 0.5\ \Omega,$ $L = 25\ \mu\text{H}$ | Fig. 11 Fig. 13 |
| Turn-Off Switching Energy, $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$ $T_{VJ} = 150^\circ\text{C}$ | E_{OFF} | | 4.8 4.8 4.9 | | | | |
| Internal Gate Resistance | $R_{G(int)}$ | | 2.53 | | Ω | $f = 100\text{ kHz}$ | |
| Input Capacitance | C_{iss} | | 25.7 | | nF | $V_{GS} = 0\text{ V}, V_{DS} = 800\text{ V},$ $V_{AC} = 25\text{ mV}, f = 100\text{ kHz}$ | Fig. 9 |
| Output Capacitance | C_{oss} | | 1.8 | | | | |
| Reverse Transfer Capacitance | C_{rss} | | 44.5 | | pF | | |
| Gate to Source Charge | Q_{GS} | | 268 | | nC | $V_{DS} = 800\text{ V}, V_{GS} = -4\text{ V}/15\text{ V},$ $I_D = 350\text{ A},$ Per IEC60747-8-4 pg 21 | |
| Gate to Drain Charge | Q_{GD} | | 244 | | | | |
| Total Gate Charge | Q_G | | 844 | | | | |
| FET Thermal Resistance, Junction to Case | $R_{th\ JC}$ | | 0.116 | | $^\circ\text{C}/\text{W}$ | | Fig. 17 |

Diode Characteristics (Per Position) ($T_{VJ} = 25^\circ\text{C}$ Unless Otherwise Specified)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions | Note |
|--|--------------|------|-------------------|------|---------------------------|--|-------------------|
| Diode Forward Voltage | V_F | | 2.0 | | V | $V_{GS} = -4\text{ V}, I_F = 350\text{ A}, T_{VJ} = 25^\circ\text{C}$ | Fig. 7 |
| | | | 2.5 | | | $V_{GS} = -4\text{ V}, I_F = 350\text{ A}, T_{VJ} = 150^\circ\text{C}$ | |
| Reverse Recovery Time | t_{RR} | | 24.5 | | ns | $V_{GS} = -4\text{ V}, I_{SD} = 350\text{ A}, V_R = 800\text{ V}$ $di/dt = 13.0\text{ A/ns}, T_{VJ} = 150^\circ\text{C}$ | Fig. 32 |
| Reverse Recovery Charge | Q_{RR} | | 5.0 | | μC | | |
| Peak Reverse Recovery Current | I_{RRM} | | 341 | | A | | |
| Reverse Recovery Energy, $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$ $T_{VJ} = 150^\circ\text{C}$ | E_{RR} | | 1.7 2.0 2.0 | | mJ | $V_{DS} = 600\text{ V}, I_D = 350\text{ A},$ $V_{GS} = -4\text{ V}/15\text{ V}, R_{G(ext)} = 0.5\ \Omega,$ $L = 25\ \mu\text{H}$ | Fig. 14 Note 5 |
| Diode Thermal Resistance, JCT. to Case | $R_{th\ JC}$ | | 0.112 | | $^\circ\text{C}/\text{W}$ | | Fig. 18 |

Note (5): SiC Schottky diodes do not have reverse recovery energy but still contribute capacitive energy



Module Physical Characteristics

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|------------------------------------|--------------------|------|------|------|------|--|
| Package Resistance, M1 (High-Side) | R ₃₋₁ | | 1.31 | | mΩ | T _C = 25 °C, I _{SD} = 350 A, Note 6 |
| | | | 1.84 | | | T _C = 125 °C, I _{SD} = 350 A, Note 6 |
| Package Resistance, M2 (Low-Side) | R ₁₋₂ | | 1.26 | | | T _C = 25 °C, I _{SD} = 350 A, Note 6 |
| | | | 1.77 | | | T _C = 125 °C, I _{SD} = 350 A, Note 6 |
| Stray Inductance | L _{Stray} | | 11.1 | | nH | Between DC- and DC+, f = 10 MHz |
| Case Temperature | T _C | -40 | | 125 | °C | |
| Mounting Torque | M _S | 4 | 5 | 5.5 | N-m | Baseplate, M6-1.0 Bolts |
| | | 4 | 5 | 5.5 | | Power Terminals, M6-1.0 Bolts |
| Weight | W | | 300 | | g | |
| Case Isolation Voltage | V _{isol} | 5 | | | kV | AC, 50 Hz, 1 minute |
| Clearance Distance | | 9 | | | mm | Terminal to Terminal |
| | | 30 | | | | Terminal to Baseplate |
| Creepage Distance | | 30 | | | | Terminal to Terminal |
| | | 40 | | | | Terminal to Baseplate |

Note (6): Total Effective Resistance (Per Switch Position) = MOSFET R_{DS(on)} + Switch Position Package Resistance

Typical Performance

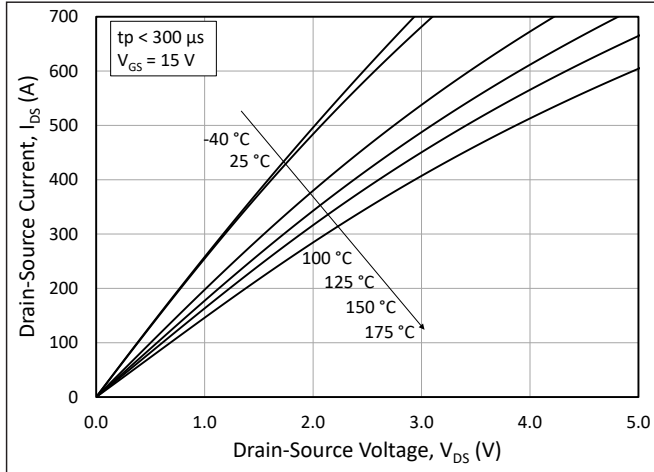


Figure 1. Output Characteristics for Various Junction Temperatures

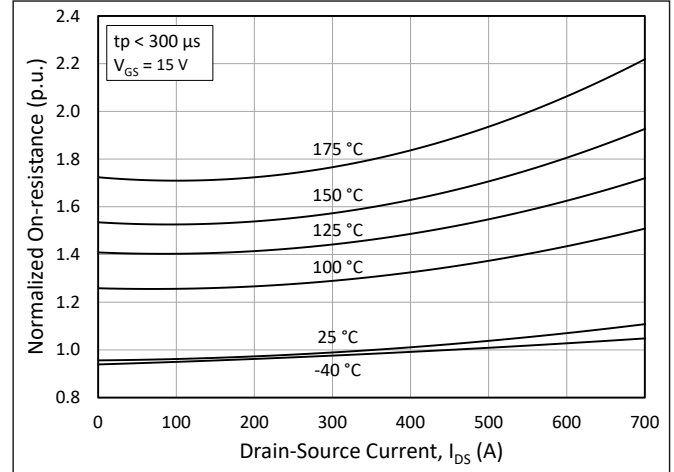


Figure 2. Normalized On-State Resistance vs. Drain Current for Various Junction Temperatures

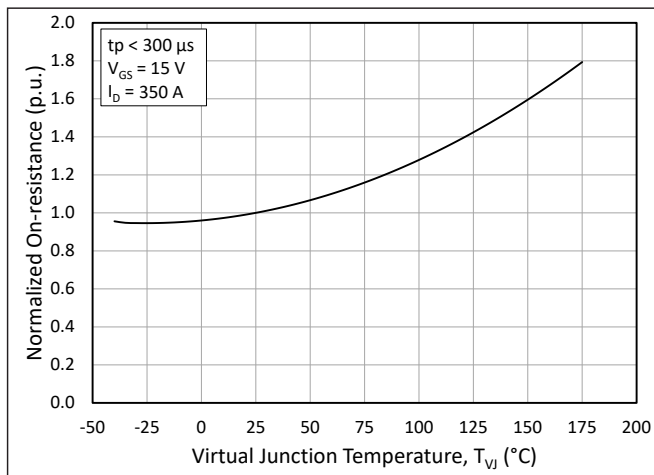


Figure 3. Normalized On-State Resistance vs. Junction Temperature

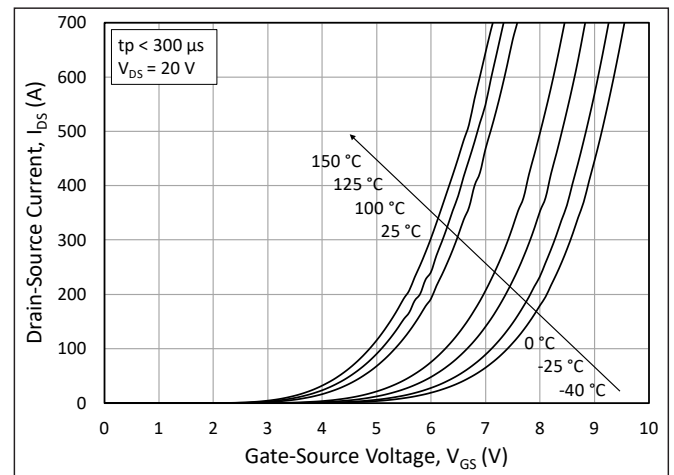


Figure 4. Transfer Characteristic for Various Junction Temperatures

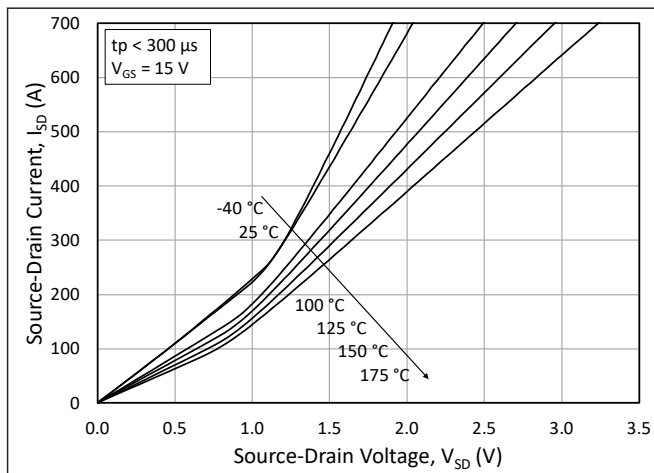


Figure 5. 3rd Quadrant Characteristic vs. Junction Temperatures at $V_{GS} = 15\text{ V}$

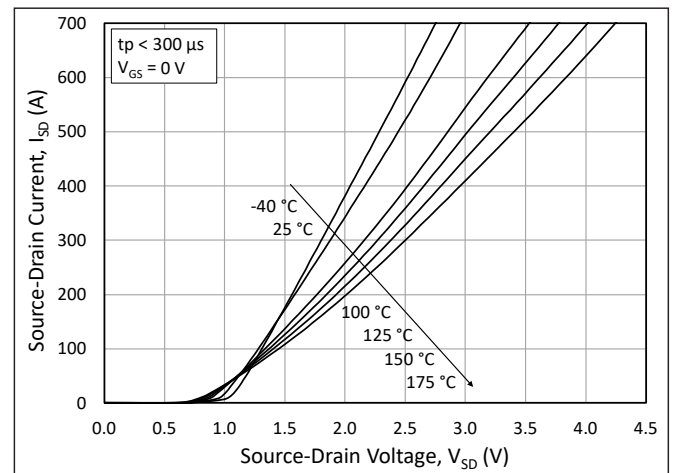


Figure 6. 3rd Quadrant Characteristic vs. Junction Temperatures at $V_{GS} = 0\text{ V}$ (Diode)

Typical Performance

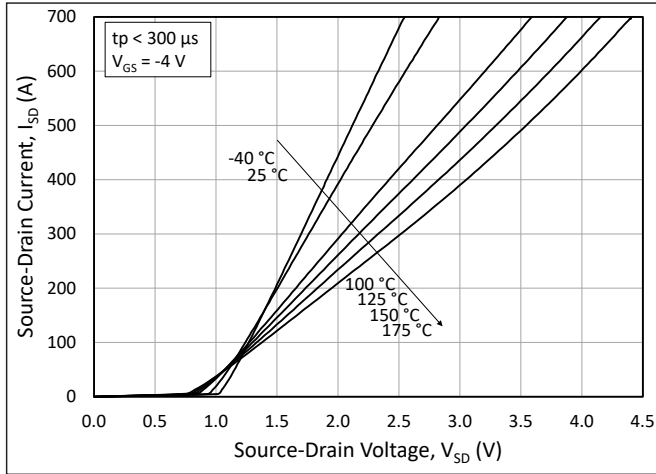


Figure 7. 3rd Quadrant Characteristic vs. Junction Temperatures at $V = -4$ V (Diode)

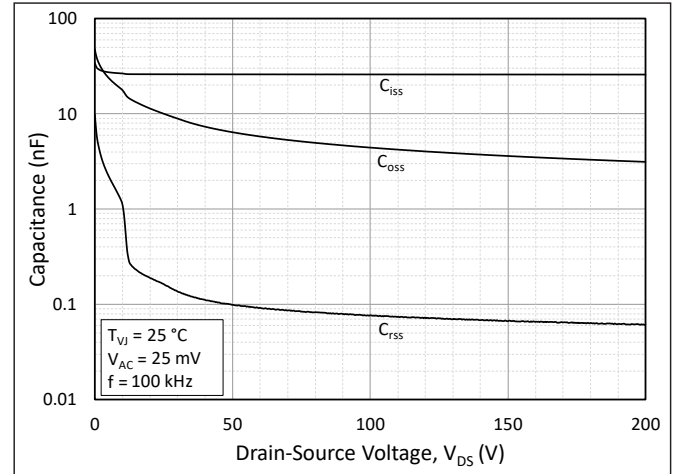


Figure 8. Typical Capacitances vs. Drain to Source Voltage (0 - 200 V)

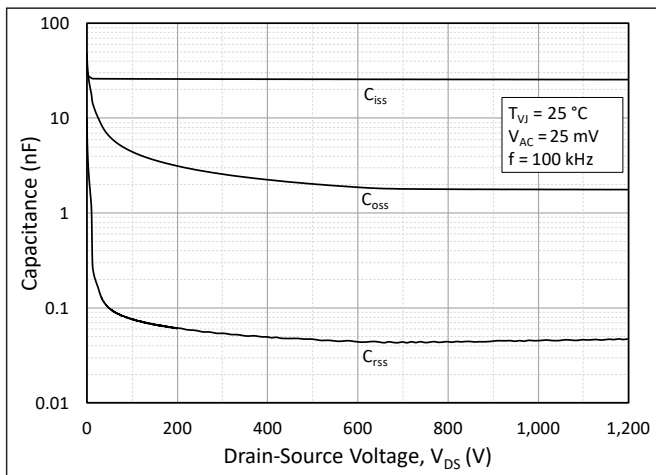


Figure 9. Typical Capacitances vs. Drain to Source Voltage (0 - 1200 V)

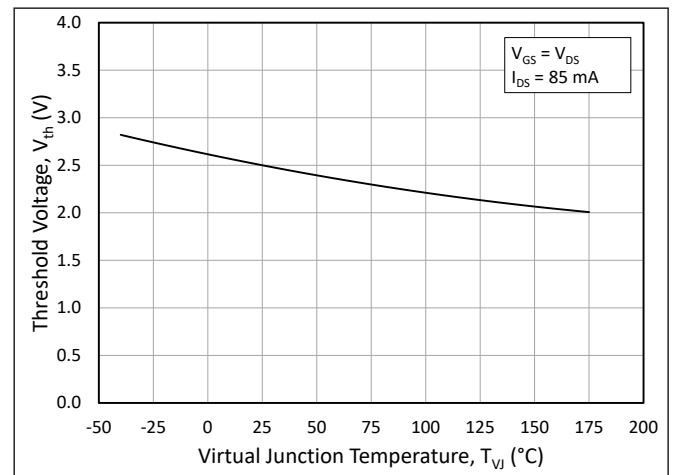


Figure 10. Threshold Voltage vs. Junction Temperature

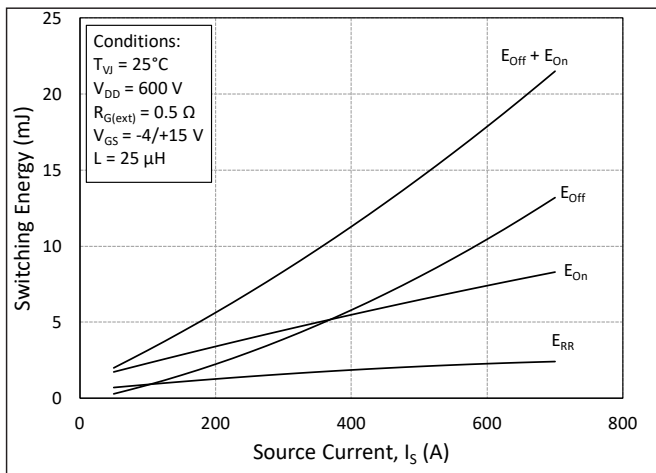


Figure 11. Switching Energy vs. Drain Current ($V_{DS} = 600$ V)

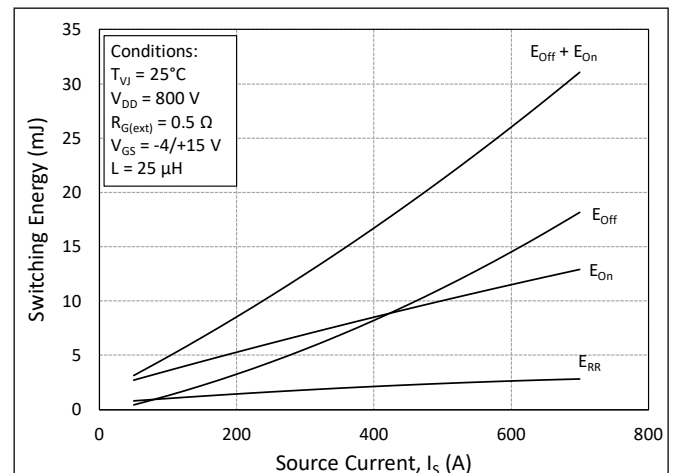


Figure 12. Switching Energy vs. Drain Current ($V_{DS} = 800$ V)

Typical Performance

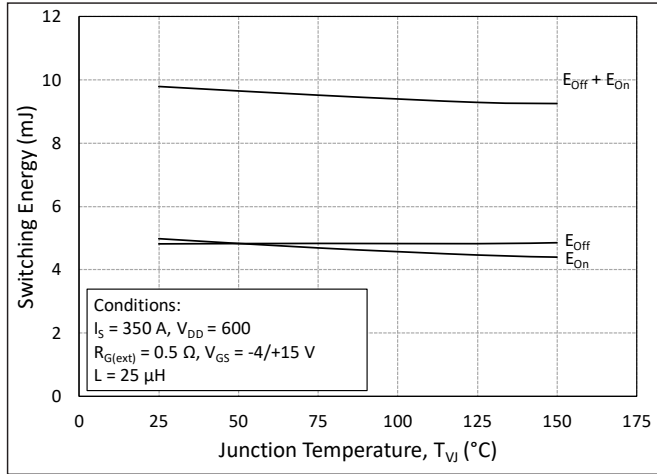


Figure 13. MOSFET Switching Energy vs. Junction Temperature

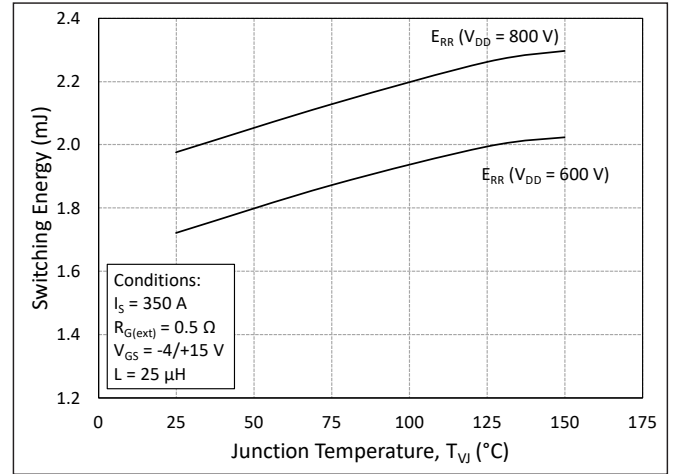


Figure 14. Reverse Recovery Energy vs. Junction Temperature

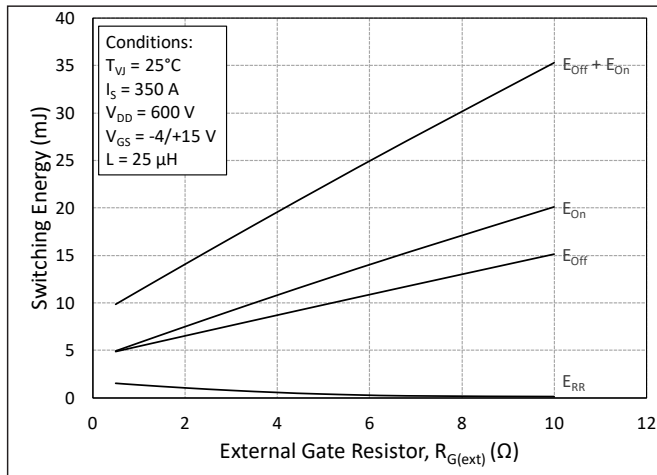


Figure 15. MOSFET Switching Energy vs. External Gate Resistance

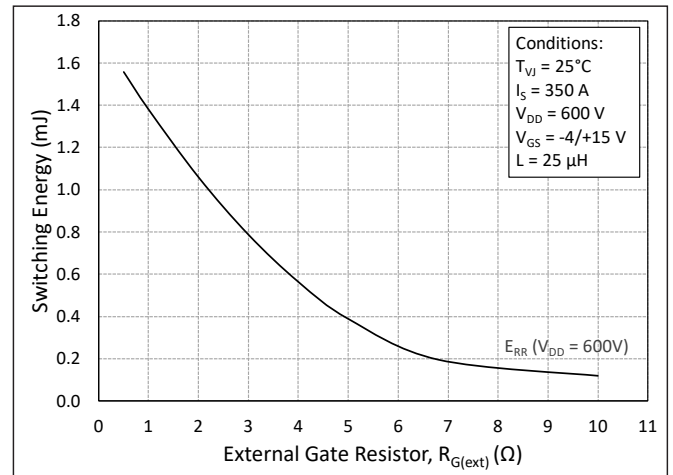


Figure 16. Reverse Recovery Energy vs. External Gate Resistance

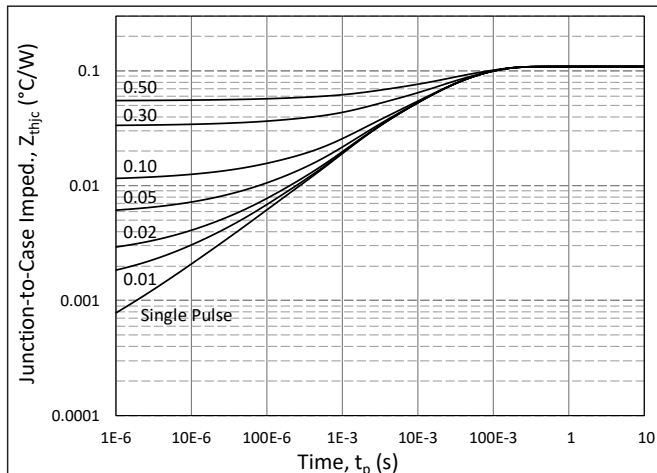


Figure 17. MOSFET Junction-to-Case Transient Thermal Impedance, $Z_{th(jc)}$ (°C/W)

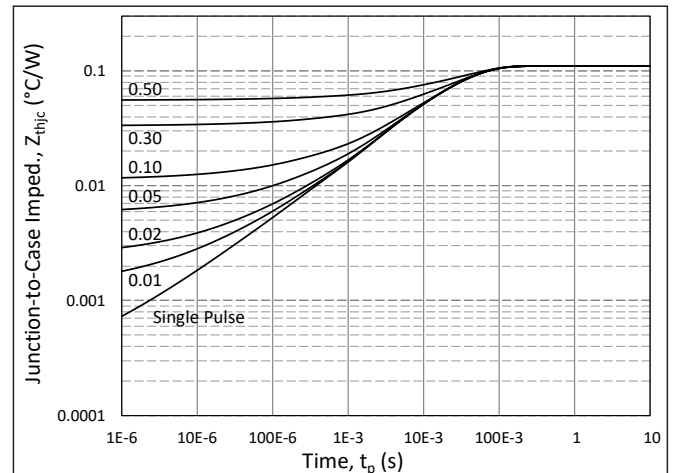


Figure 18. Diode Junction-to-Case Transient Thermal Impedance, $Z_{th(jc)}$ (°C/W)

Typical Performance

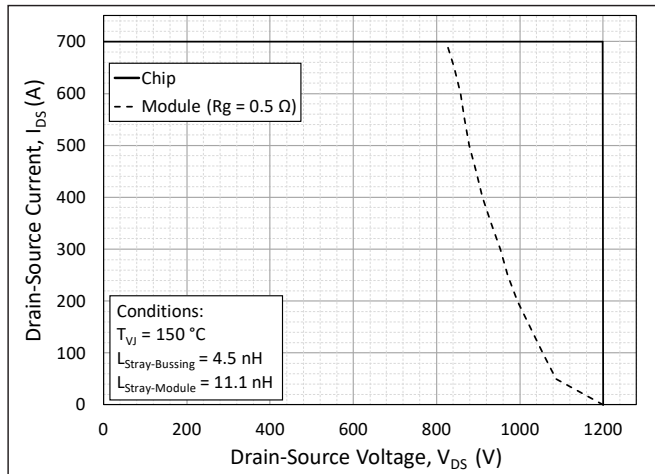


Figure 19. Switching Safe Operating Area

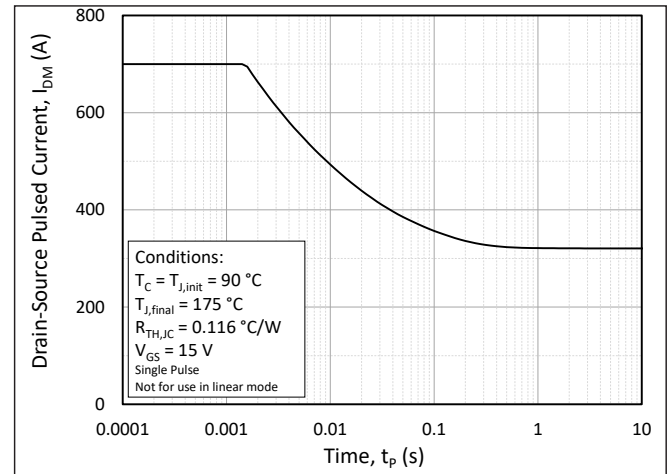


Figure 20. Pulsed Current Safe Operating Area

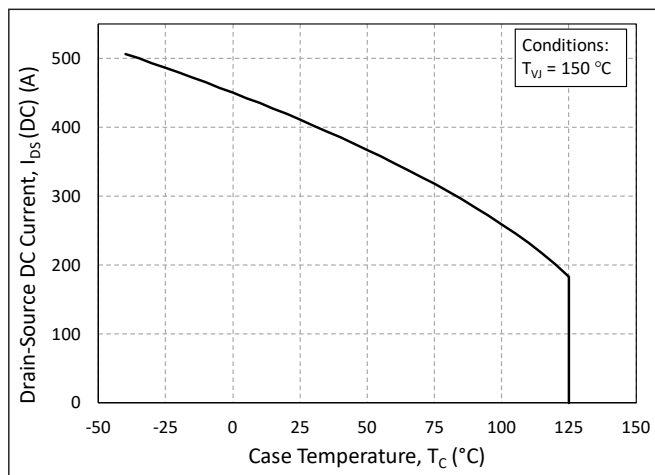


Figure 21. Continuous Drain Current Derating vs. Case Temperature

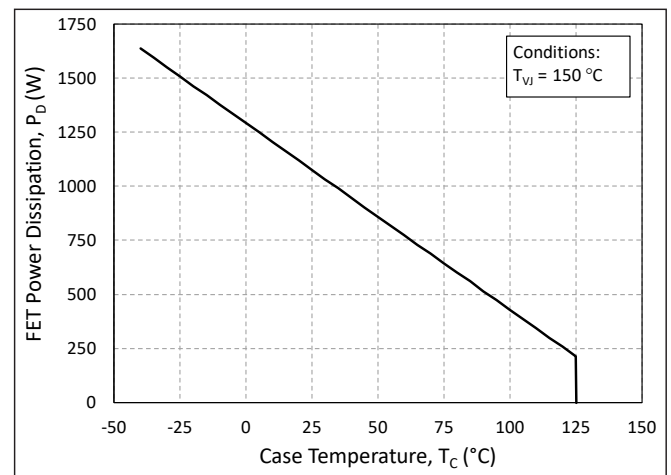


Figure 22. Maximum Power Dissipation Derating vs. Case Temperature

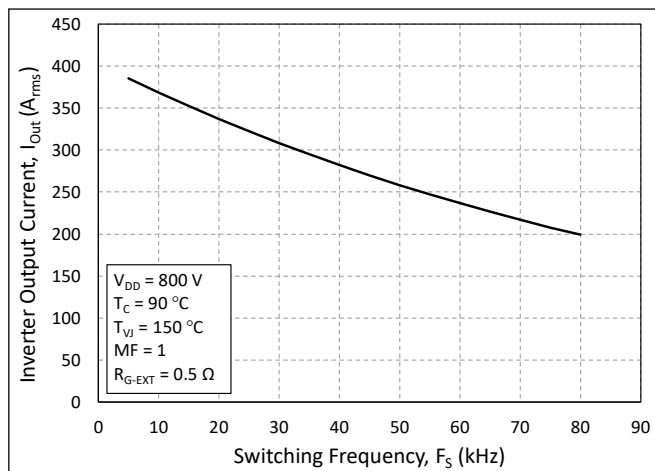


Figure 23. Typical Output Current Capability vs. Switching Frequency (Inverter Application)

Timing Characteristics

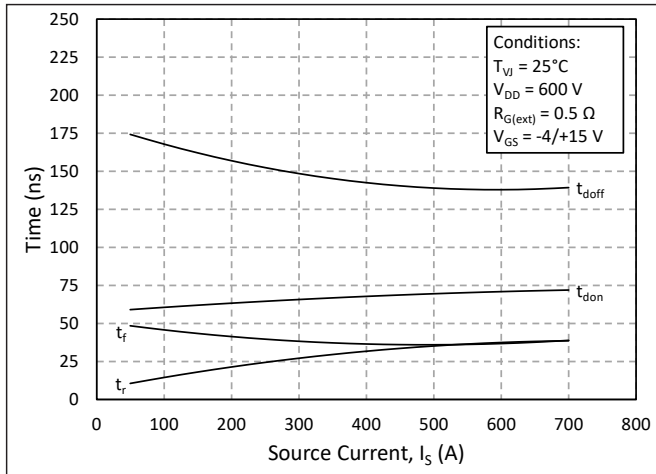


Figure 24. Timing vs. Source Current

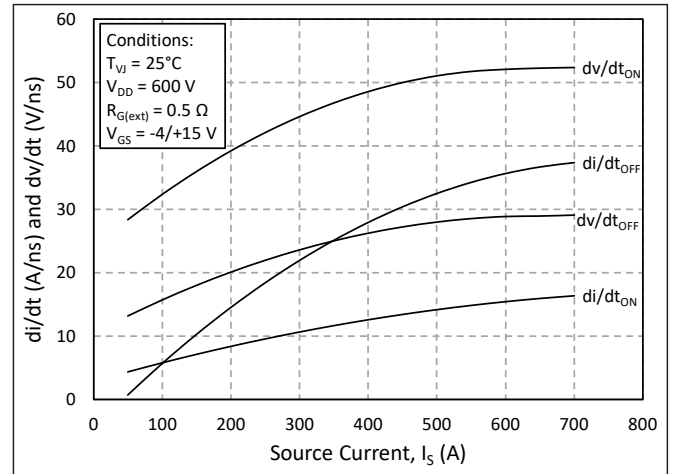


Figure 25. dv/dt and di/dt vs. Source Current

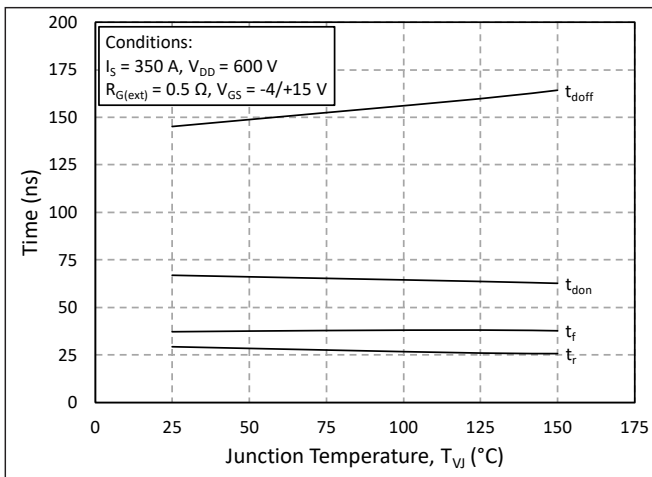


Figure 26. Timing vs. Junction Temperature

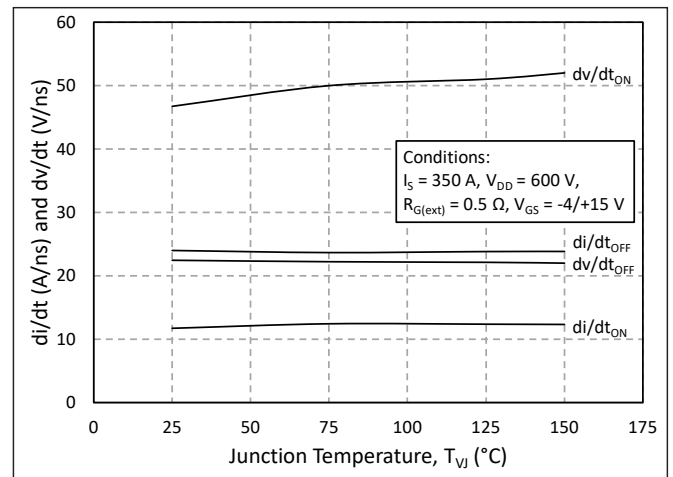


Figure 27. dv/dt and di/dt vs. Junction Temperature

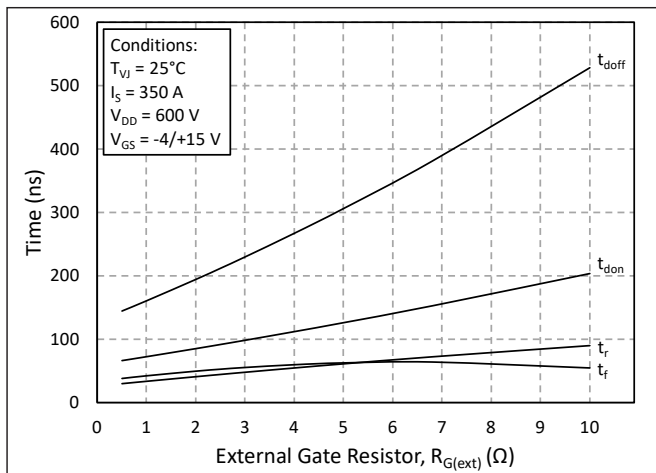


Figure 28. Timing vs. External Gate Resistance

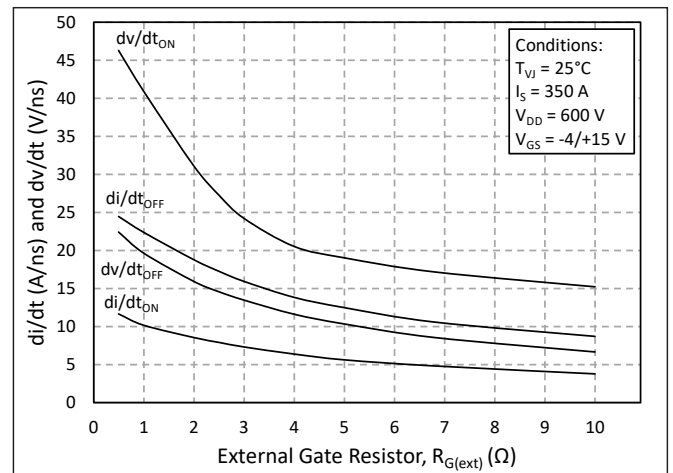


Figure 29. dv/dt and di/dt vs. External Gate Resistance

Definitions

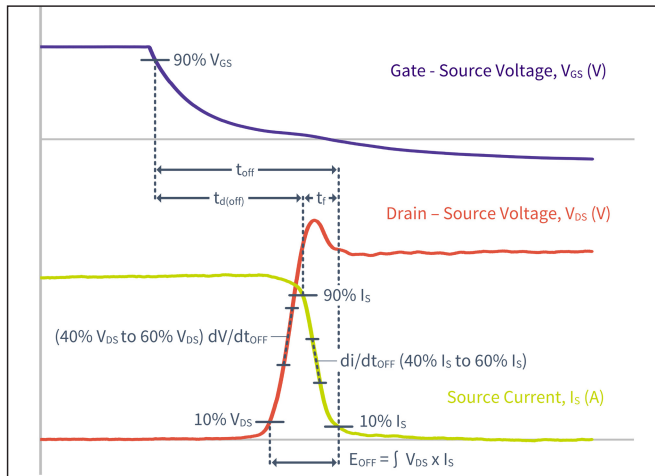


Figure 30. Turn-Off Transient Definitions

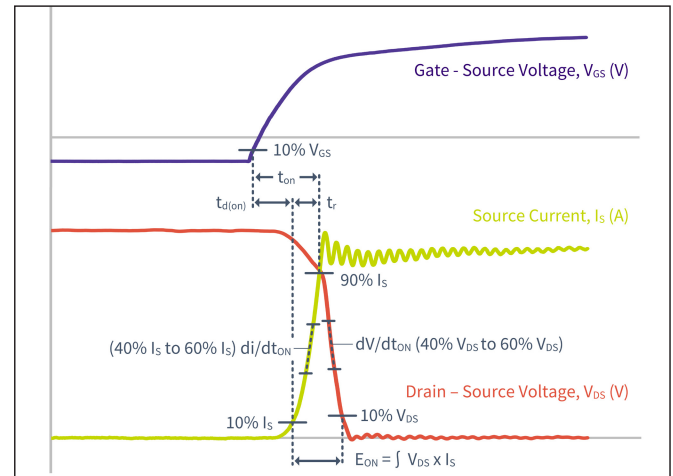


Figure 31. Turn-On Transient Definitions

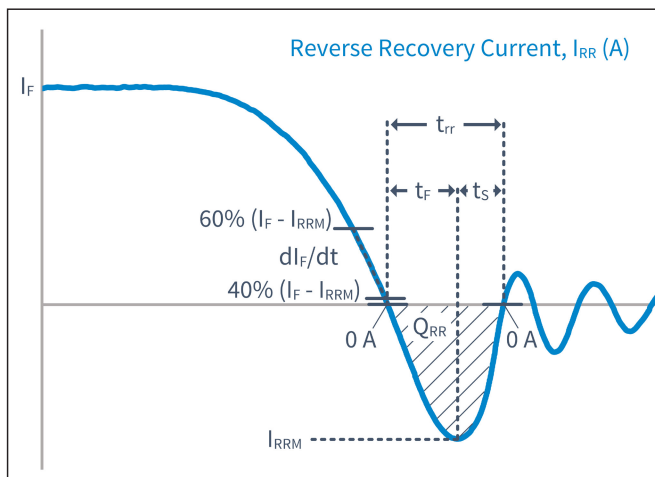


Figure 32. Reverse Recovery Definitions

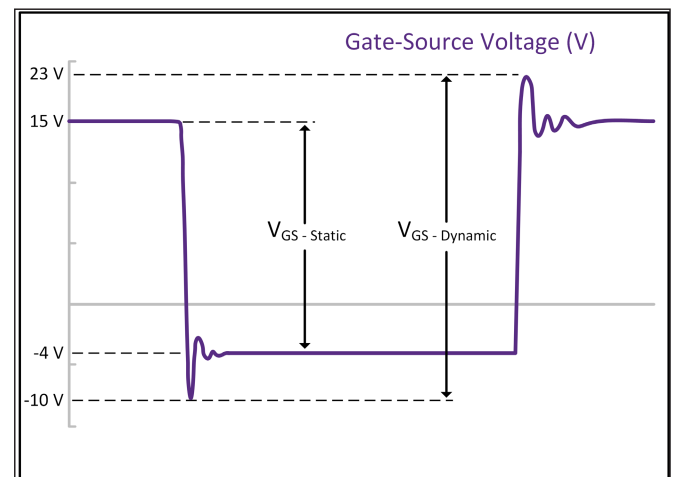
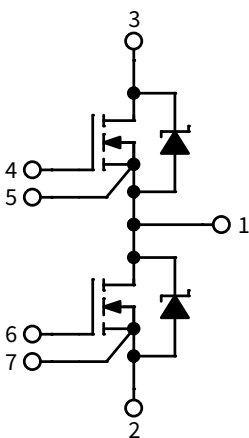
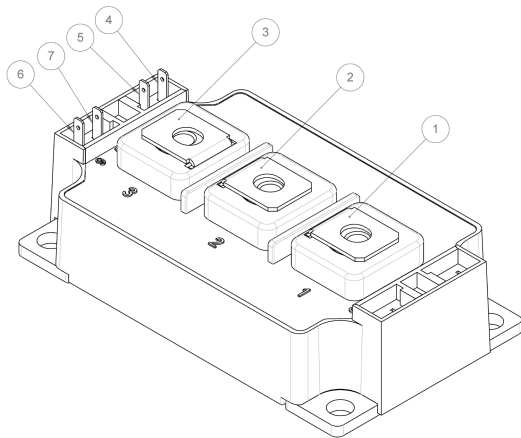


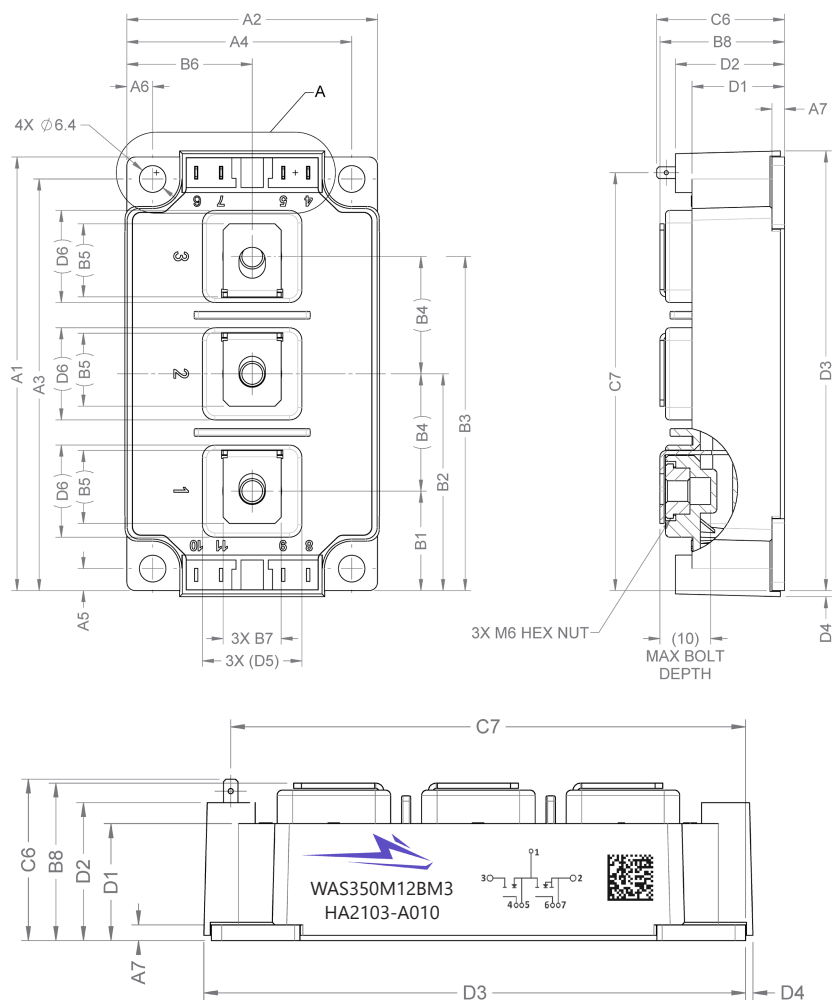
Figure 33. V_{GS} Transient Definitions



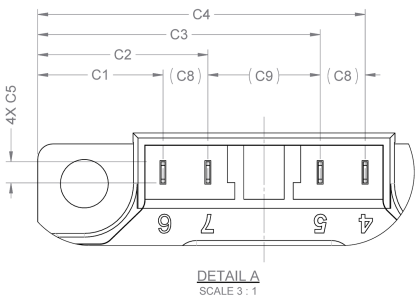
Schematic and Pin Out



Package Dimension (mm)



| DIMENSION TABLE | | |
|-----------------|-----------|-----------|
| SYMBOL | DIMENSION | TOLERANCE |
| A1 | 103.5 | ±0.30 |
| A2 | 60.44 | ±0.30 |
| A3 | 98.25 | ±0.30 |
| A4 | 54.22 | ±0.30 |
| A5 | 5.25 | ±0.30 |
| A6 | 6.22 | ±0.30 |
| A7 | 3 | ±0.30 |
| B1 | 23.75 | ±0.40 |
| B2 | 51.75 | ±0.40 |
| B3 | 79.75 | ±0.40 |
| B4 | (28) | REF. |
| B5 | (17.43) | REF. |
| B6 | 30.23 | ±0.40 |
| B7 | (14) | REF. |
| B8 | 30.03 | ±0.40 |
| C1 | 16.73 | ±0.40 |
| C2 | 22.73 | ±0.40 |
| C3 | 37.73 | ±0.40 |
| C4 | 43.73 | ±0.40 |
| C5 | 2.8 | ±0.40 |
| C6 | 30.8 | ±0.50 |
| C7 | 99.75 | ±0.40 |
| C8 | (6) | REF. |
| C9 | (15) | REF. |
| D1 | 22.3 | ±0.30 |
| D2 | 26.3 | ±0.30 |
| D3 | 104.95 | ±0.30 |
| D4 | 1.45 | ±0.40 |
| D5 | (24) | REF. |
| D6 | (22) | REF. |





Product Ordering Code

| Part Number | Description |
|---------------|---|
| WAS350M12BM3 | Without Pre-Applied Phase Change Thermal Interface Material |
| WAS350M12BM3T | With Pre-Applied Phase Change Thermal Interface Material |

Supporting Links & Tools

Simulation Tools & Support

- [All LTSpice Models](#)
- [All PLECS Models](#)
- [SpeedFit 2.0 Design Simulator™](#)
- [Technical Support Forum](#)

Compatible Evaluation Hardware

- [CGD1200HB2P-BM3: Dual Channel Differential Isolated Half Bridge Gate Driver Board](#)
- [KIT-CRD-CIL12N-BM: Dynamic Performance Evaluation Board for the BM2 and BM3 Module](#)
- [CGD1700HB2P-BM3: Evaluation Gate Driver Tool Optimized for the 1700 V BM3 Power Modules](#)
- [KIT-CRD-CIL17N-BM: Dynamic Characterization Evaluation Tool Optimized for 1700 V BM Power Modules](#)
- [CGD12HB00D: Differential Transceiver Daughter Board Companion Tool for Differential Gate Drivers](#)

Application Notes

- [PRD-07933: Wolfspeed Power Module Thermal Interface Material Application User Guide](#)
- [PRD-06379: Environmental Considerations for Power Electronics](#)
- [PRD-08710: Measuring Stray Inductance in Power Electronic Systems](#)
- [PRD-07845: Power Module Baseplate Capacitance and Electromagnetic Compatibility](#)
- [PRD-08376: Thermal Characterization Methods and Applications](#)
- [PRD-06933: Capacitance Ratio and Parasitic Turn-On](#)



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